30 V, 3 A, Low $V_{CE(sat)}$ NPN Transistor

NSS30201MR6T1G, SNSS30201MR6T1G

onsemi's e^2PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical application are DC−DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e^2PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

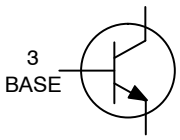
Features

- AEC−Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These are Pb−Free Devices*

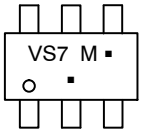
*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

30 VOLTS
3.0 AMPS
NPN LOW $V_{CE(sat)}$ TRANSISTOR
EQUIVALENT $R_{DS(on)}$ 100 mΩ

TSOP−6
CASE 318G
STYLE 6



DEVICE MARKING



VS7 = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NSS30201MR6T1G	TSOP−6 (Pb−Free)	3,000 / Tape & Reel
SNSS30201MR6T1G	TSOP−6 (Pb−Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	30	V
Collector-Base Voltage	V_{CBO}	50	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current – Continuous	I_C	2.0	A
Collector Current – Peak	I_{CM}	3.0	A

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation T_A = 25°C Derate above 25°C	P_D (Note 1)	 535 4.3	 mW mW/°C
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$ (Note 1)	 234	°C/W
Total Device Dissipation T_A = 25°C Derate above 25°C	P_D (Note 2)	 1.180 9.4	 W mW/°C
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$ (Note 2)	 106	°C/W
Thermal Resistance, Junction–to–Lead #1	$R_{\theta JL}$ (Note 1) $R_{\theta JL}$ (Note 2)	110 50	°C/W °C/W
Total Device Dissipation (Single Pulse < 10 s)	$P_{Dsingle}$ (Notes 2 and 3)	 1.75	W
Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR–4 with 1 oz and 3.9 mm^2 of copper area.
2. FR–4 with 1 oz and 645 mm^2 of copper area.
3. Refer to Figure 8.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector−Emitter Breakdown Voltage (I_C = 10 mA, I_B = 0)	$V_{(BR)CEO}$	30	–	–	V
Collector−Base Breakdown Voltage (I_C = 0.1 mA, I_E = 0)	$V_{(BR)CBO}$	50	–	–	V
Emitter−Base Breakdown Voltage (I_E = 0.1 mA, I_C = 0)	$V_{(BR)EBO}$	5.0	–	–	V
Collector Cutoff Current (V_{CB} = 30 V, I_E = 0)	I_{CBO}	–	–	0.1	μA
Collector−Emitter Cutoff Current (V_{CES} = 30 V)	I_{CES}	–	–	0.1	μA
Emitter Cutoff Current (V_{EB} = 4.0 V)	I_{EBO}	–		0.1	μA
ON CHARACTERISTICS					
DC Current Gain (Note 4) (I_C = 1.0 mA, V_{CE} = 5.0 V) (I_C = 0.5 A, V_{CE} = 5.0 V) (I_C = 1.0 A, V_{CE} = 5.0 V)	h_{FE}	300 300 200	– 500 –	– 900 –	
Collector−Emitter Saturation Voltage (Note 4) (I_C = 1.0 A, I_B = 100 mA) (I_C = 0.5 A, I_B = 50 mA) (I_C = 0.1 A, I_B = 1.0 mA)	$V_{CE(sat)}$	– – –	0.10 0.06 0.05	0.200 0.125 0.075	V
Base−Emitter Saturation Voltage (Note 4) (I_C = 1.0 A, I_B = 0.1 A)	$V_{BE(sat)}$	–	–	1.1	V
Base−Emitter Turn−on Voltage (Note 4) (I_C = 1.0 A, V_{CE} = 2.0 V)	$V_{BE(on)}$	–	–	1.1	V
Cutoff Frequency (I_C = 100 mA, V_{CE} = 5.0 V, f = 100 MHz	f_T	200	300	–	MHz
Output Capacitance (f = 1.0 MHz)	C_{obo}	–	–	15	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulsed Condition: Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

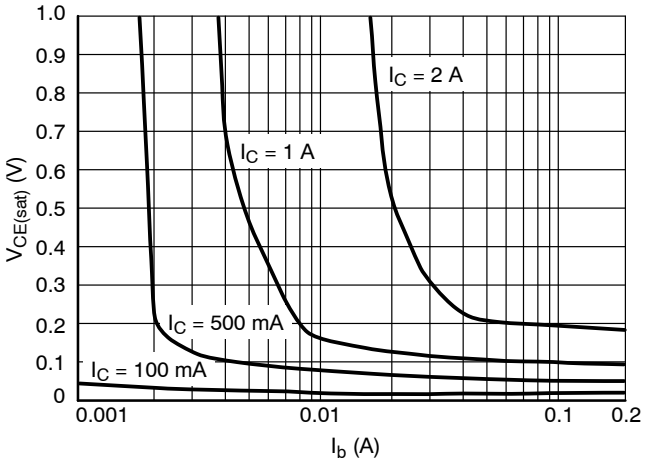


Figure 1. $V_{CE\ (sat)}$ versus I_b

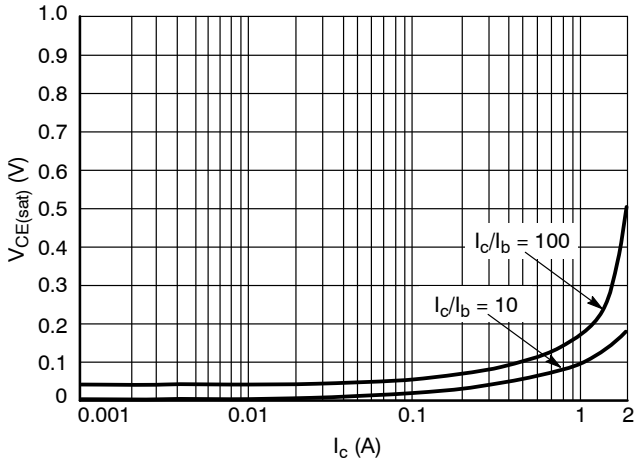


Figure 2. $V_{CE\ (sat)}$ versus I_c

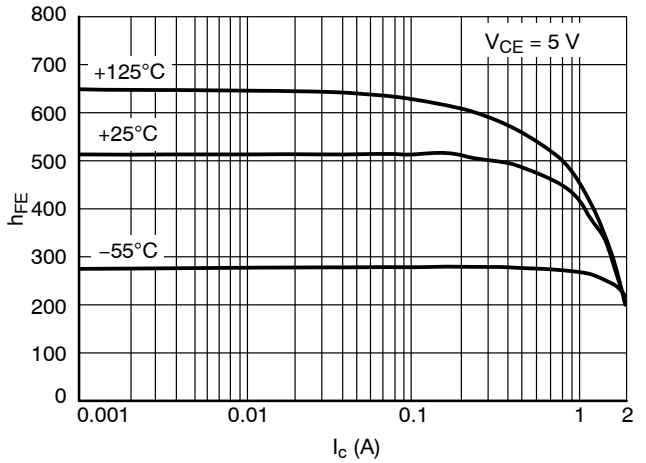


Figure 3. h_{FE} versus I_c

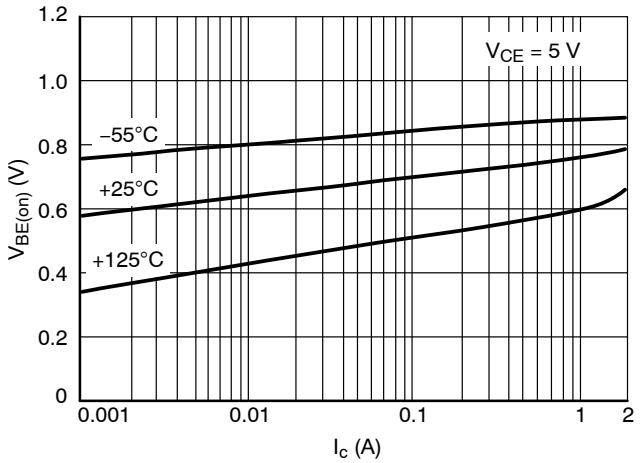


Figure 4. $V_{BE(on)}$ versus I_c

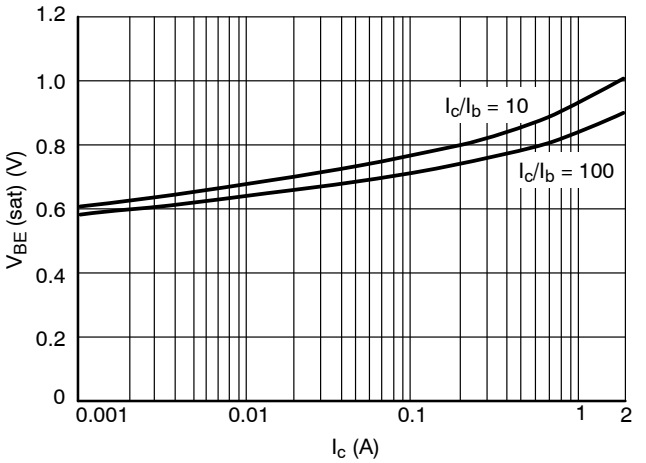


Figure 5. $V_{BE(sat)}$ versus I_c

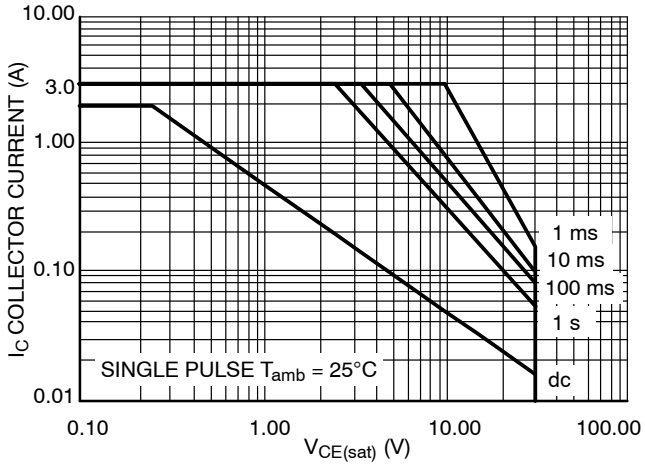


Figure 6. Safe Operating Area

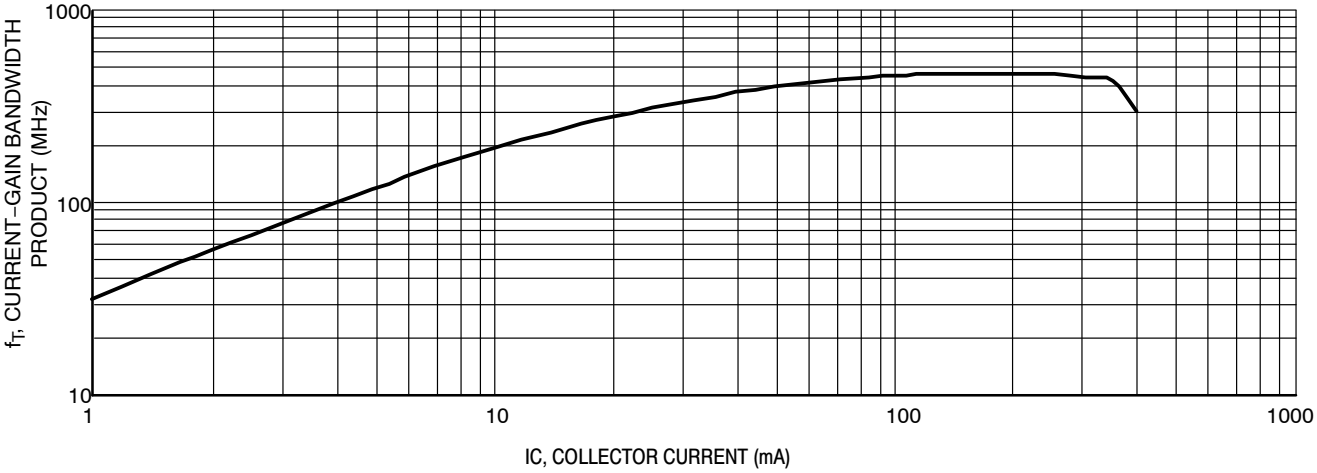


Figure 7. f_T (MHZ) versus I_C (mA)
V_{CE} = 5.0 V

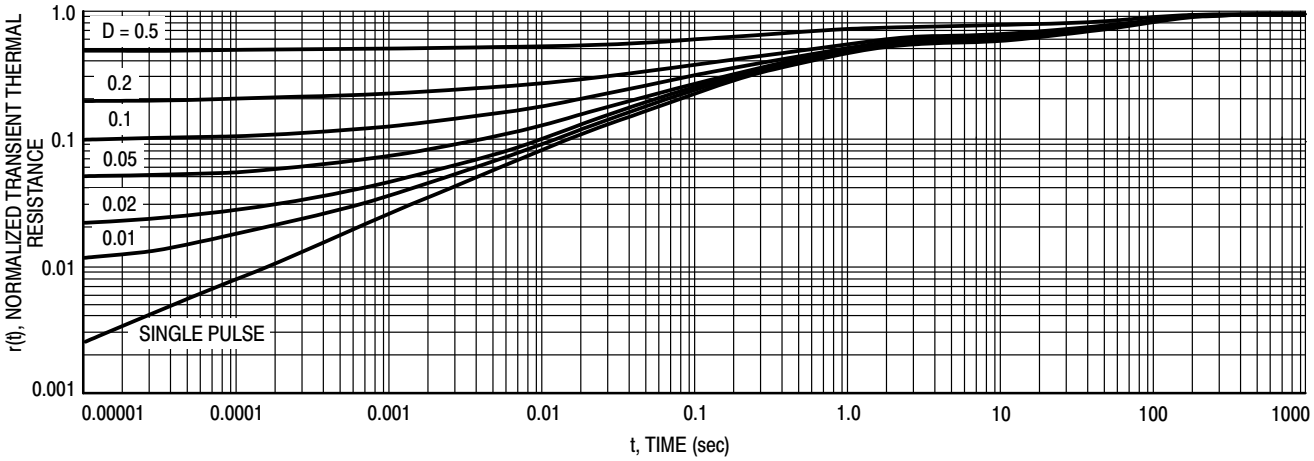
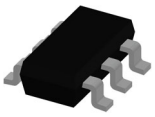
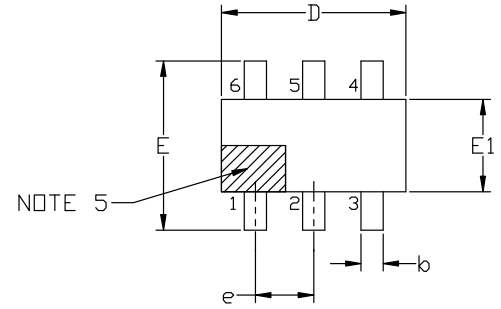


Figure 8. Normalized Thermal Response



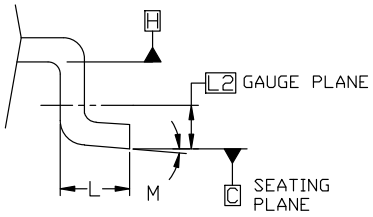
TSOP−6 3.00x1.50x0.90, 0.95P
CASE 318G
ISSUE W

DATE 26 FEB 2024

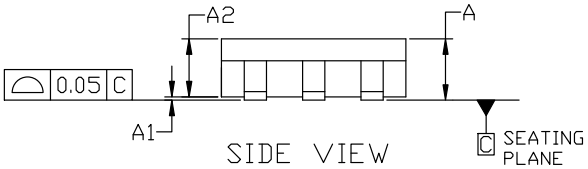


TOP VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
5. PIN 1 INDICATOR MUST BE LOCATED IN THE INDICATED ZONE

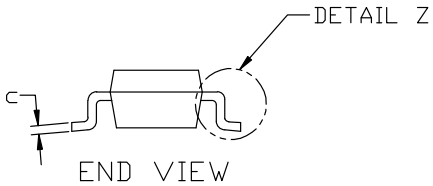


DETAIL Z
SCALE 3:1

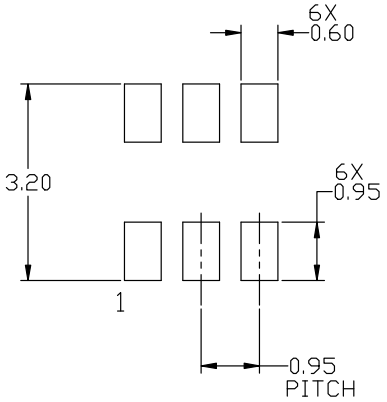


SIDE VIEW

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.01	0.06	0.10
A2	0.80	0.90	1.00
b	0.25	0.38	0.50
c	0.10	0.18	0.26
D	2.90	3.00	3.10
E	2.50	2.75	3.00
E1	1.30	1.50	1.70
e	0.85	0.95	1.05
L	0.20	0.40	0.60
L2	0.25 BSC		
M	0°	---	10°



END VIEW



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download th e ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

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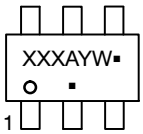
CASE 318G
ISSUE W

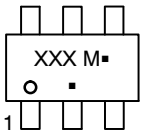
DATE 26 FEB 2024

GENERIC MARKING DIAGRAM*



IC

XXX = Specific Device Code
A =Assembly Location
Y = Year
W = Work Week
▪ = Pb−Free Package



STANDARD

XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 2:
PIN 1. EMITTER 2
2. BASE 1
3. COLLECTOR 1
4. EMITTER 1
5. BASE 2
6. COLLECTOR 2

STYLE 3:
PIN 1. ENABLE
2. N/C
3. R BOOST
4. Vz
5. V in
6. V out

STYLE 4:
PIN 1. N/C
2. V in
3. NOT USED
4. GROUND
5. ENABLE
6. LOAD

STYLE 5:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

STYLE 6:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 7:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. N/C
5. COLLECTOR
6. EMITTER

STYLE 8:
PIN 1. Vbus
2. D(in)
3. D(in)+
4. D(out)+
5. D(out)
6. GND

STYLE 9:
PIN 1. LOW VOLTAGE GATE
2. DRAIN
3. SOURCE
4. DRAIN
5. DRAIN
6. HIGH VOLTAGE GATE

STYLE 10:
PIN 1. D(OUT)+
2. GND
3. D(OUT)−
4. D(IN)−
5. VBUS
6. D(IN)+

STYLE 11:
PIN 1. SOURCE 1
2. DRAIN 2
3. DRAIN 2
4. SOURCE 2
5. GATE 1
6. DRAIN 1/GATE 2

STYLE 12:
PIN 1. I/O
2. GROUND
3. I/O
4. I/O
5. VCC
6. I/O

STYLE 13:
PIN 1. GATE 1
2. SOURCE 2
3. GATE 2
4. DRAIN 2
5. SOURCE 1
6. DRAIN 1

STYLE 14:
PIN 1. ANODE
2. SOURCE
3. GATE
4. CATHODE/DRAIN
5. CATHODE/DRAIN
6. CATHODE/DRAIN

STYLE 15:
PIN 1. ANODE
2. SOURCE
3. GATE
4. DRAIN
5. N/C
6. CATHODE

STYLE 16:
PIN 1. ANODE/CATHODE
2. BASE
3. EMITTER
4. COLLECTOR
5. ANODE
6. CATHODE

STYLE 17:
PIN 1. EMITTER
2. BASE
3. ANODE/CATHODE
4. ANODE
5. CATHODE
6. COLLECTOR

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